

Docket No. 241807US2 DIV

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

IN RE APPLICATION OF: Toshiaki IWAMATSU et al.

SERIAL NO: New Application

GAU:

FILED: Herewith

EXAMINER:

FOR: SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME

**INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97**

COMMISSIONER FOR PATENTS  
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

**REFERENCES**

- ☒ The applicant(s) wish to make of record the references listed on the attached form PTO-1449 that were cited in the parent application Serial No. 09/985,020, filed November 1, 2001. Copies of the listed references were filed in the parent application.
- ☐ A check is attached in the amount required under 37 CFR §1.17(p).

**RELATED CASES**

- ☐ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check is attached in the amount required under 37 CFR §1.17(p).

**CERTIFICATION**

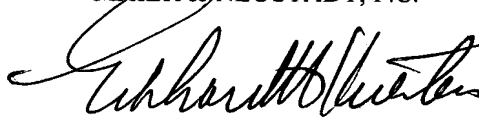
- ☐ Each item of information contained in this information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

**DEPOSIT ACCOUNT**

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment form is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

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Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. <b>241807US2DIV</b>		SERIAL NO. <b>New Application</b>	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT <b>Toshiaki IWAMATSU et al.</b>			
				FILING DATE <b>Herewith</b>		GROUP	
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA	6,261,882	07/2001	Kim			
	AB	6,097,103	08/2000	Ishigaki			
	AC	5,956,617	09/1999	Kimura et al.			
	AD	5,612,243	03/1997	Verrett			
	AE	5,294,822	03/1994	Verrett			
	AF	5,223,456	06/1993	Malwah			
	AG	4,786,611	11/1988	Pfiester			
	AH	4,476,482	10/1984	Scott et al.			
	AI	4,374,700	02/1983	Scott et al.			
	AJ						
	AK						
	AL						
	AM						
	AN						
<b>FOREIGN PATENT DOCUMENTS</b>							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES                  NO		
	AO	2-159035	06/19/90	JAPAN (w/ English Extract)		X	
	AP	9-275134	10/21/97	JAPAN (w/ English Extract)		X	
	AQ	6-204334	07/22/94	JAPAN (w/ English Extract)		X	
	AR						
	AS						
	AT						
	AU						
	AV						
<b>OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)</b>							
	AW	M. INOHARA, et al., "Copper Contamination Induced Degradation of MOSFET Characteristics and Reliability", 2000 Symposium on VLSI Technology Digest of Technical Papers, IEEE, 2000, pgs. 26-27					
	AX	Kazuyuki HOZAWA, et al., "Copper distribution behavior near a SiO <sub>2</sub> /Si interface by low-temperature (<400°C) annealing and its influence on electrical characteristics of MOS-capacitors", 2000 Symposium on VLSI Technology Digest of Technical Papers, IEEE, 2000, pgs. 24-25					
	AY	A. STEEGEN, et al., "Silicide and Shallow Trench Isolation line width dependent stress induced junction leakage", 2000 Symposium on VLSI Technology Digest of Technical Papers, IEEE, 2000, pgs. 180-181					
	AZ					<input type="checkbox"/> Additional References sheet(s) attached	
Examiner							
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							